SGS-THOMSON MICROELECTRONICS

L3121B

Application Specific Discretes
A.S.D.™

PROGRAMMABLE TRANSIENT VOLTAGE SUPPRESSOR FOR SLIC PROTECTION

FEATURES

- BIDIRECTIONAL FUNCTION WITH VOLTAGE PROGRAMMABILITY IN BOTH POSITIVE AND NEGATIVE POLARITIES.
- PROGRAMMABLE BREAKDOWN VOLTAGE UP TO 100 V.
- HOLDING CURRENT = 150 mA min.
- HIGH SURGE CURRENT CAPABILITY. $I_{PP} = 100A$, $10/1000 \mu s$


SIP 4

DESCRIPTION

This device has been especially designed to protect a subscriber line interface circuit (SLIC) with an integrated ring generator.

Used with the recommended application circuit, each line (TIP and RING) is protected against positive and negative surges. In the positive polarity, the breakdown voltage is referenced to the + VB , and in the negative polarity, the breakdown voltage is referenced to the -Vbat .

Its high surge current capability makes the L3121B a reliable protection device for very exposed equipment, or when series resistors are very low.

SCHEMATIC DIAGRAM

IN ACCORDANCE WITH FOLLOWING STANDARDS

|		
CCITT K20	10/700 µs	1 kV
	5/310 µs	25 A
VDE 0433	10/700 µs	2 kV
	5/310 µs	50 A
CNET	0.5/700 µs	1 kV
	0.2/310 µs	25 A
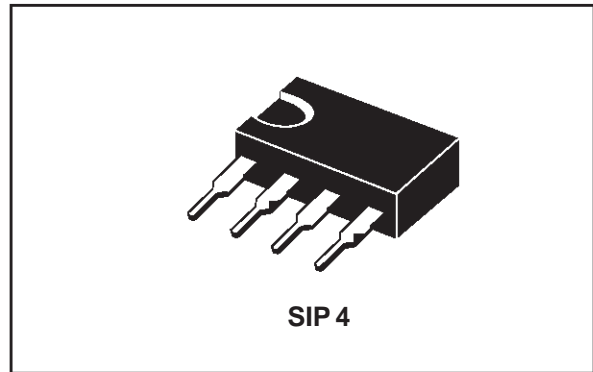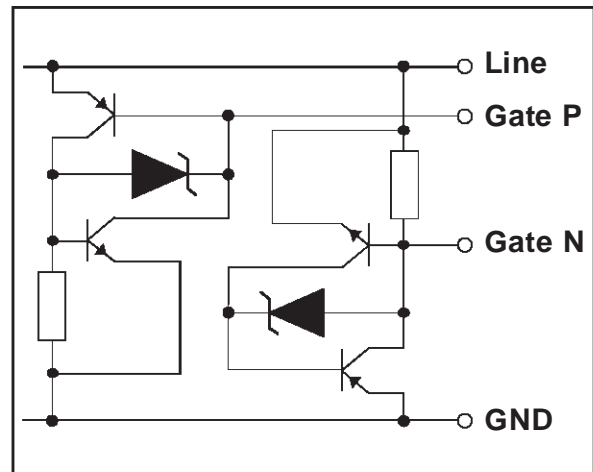
CONNECTION DIAGRAM
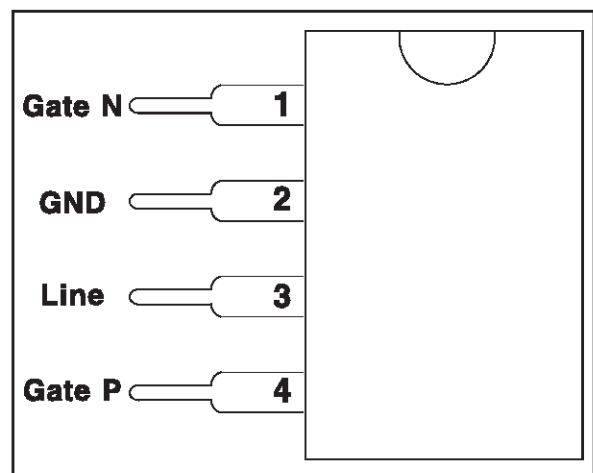
TM: ASD is trademarks of SGS-THOMSON Microelectronics.
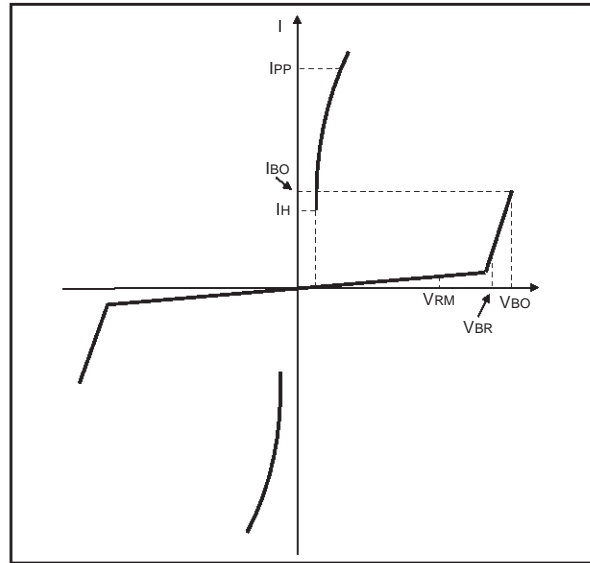
ABSOLUTE MAXIMUM RATINGS (Tamb = 25°C)

Symbol	Parameter		Value	Unit
I_{PP}	Peak pulse current	10/1000 µs 8/20 µs	100 250	A
I_{TSM}	Non repetitive surge peak on-state current	tp = 10 ms	50	A
V_{MLG} V_{MGL}	Maximum voltage LINE/GND. Maximum voltage GATE/LINE.		100 80	V V
T_{stg} T_j	Storage temperature range Maximum operating junction temperature		- 40 to + 150 + 150	°C °C
T_L	Maximum lead temperature for soldering during 10s		260	°C

Pulse waveform 10/1000µs
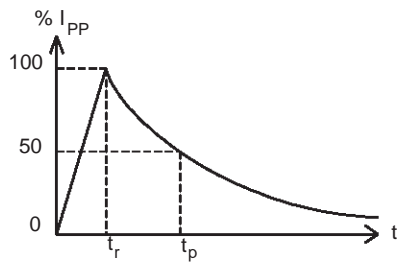
THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th\ (j-a)}$	Junction-to-ambient	80	°C/W

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ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\,°C$)

Symbol	Parameter
V_{RM}	Stand-off voltage
I_{RM}	Reverse leakage current
V_{BR}	Breakdown voltage
V_{BO}	Breakover voltage
I_H	Holding current
I_{BO}	Breakover current
I_{PP}	Peak pulse current
V_{GN}	Gate voltage
I_{GN}, I_{GP}	Triggering gate current
C	Capacitance

1- OPERATION WITHOUT GATE

Type	I_{RM} @ V_{RM}		V_{BR} @ I_R		V_{BO}	@	I_{BO}	I_H	C
	max.		min.		max.	typ.	max.	min.	max.
						note 1		note 1	note 2
	μA	V	V	mA	V	mA	mA	mA	pF
L3121B	5 8	60 90	100	1	180	200	500	150	200

2- OPERATION WITH GATE

Type	V_{GN} @ I_{GN} = 200mA		I_{GN} @ V_{AC} = 60V		I_{GP} @ V_{AC} = 60V
	min.	max.	min.	max.	max.
	V	V	mA	mA	mA
L3121B	0.6	1.8	80	200	180

Note 1 : See the reference test circuits for I_H, I_{BO} and V_{BO} parameters.

Note 2 : V_R = 5 V, F = 1MHz.

REFERENCE TEST CIRCUIT FOR I$_{BO}$ and V$_{BO}$ parameters :

t p = 20ms

Auto
Transformer
220V/2A

static
relay.

R1
140 Ω

R2
240 Ω

220V

V$_{out}$

K

I$_{BO}$, I$_H$
measure

D.U.T

V$_{BO}$
measure

Transformer
220V/800V
5A

TEST PROCEDURE :

■ Pulse Test duration (tp = 20ms):
- For Bidirectional devices = Switch K is closed
- For Unidirectional devices = Switch K is open.

■ V$_{OUT}$ Selection
- Device with V$_{BO}$ < 200 Volt
     - V$_{OUT}$ = 250 V$_{RMS}$, R$_1$ = 140 Ω.
- Device with V$_{BO}$ ≥ 200 Volt
     - V$_{OUT}$ = 480 V$_{RMS}$, R$_2$ = 240 Ω.
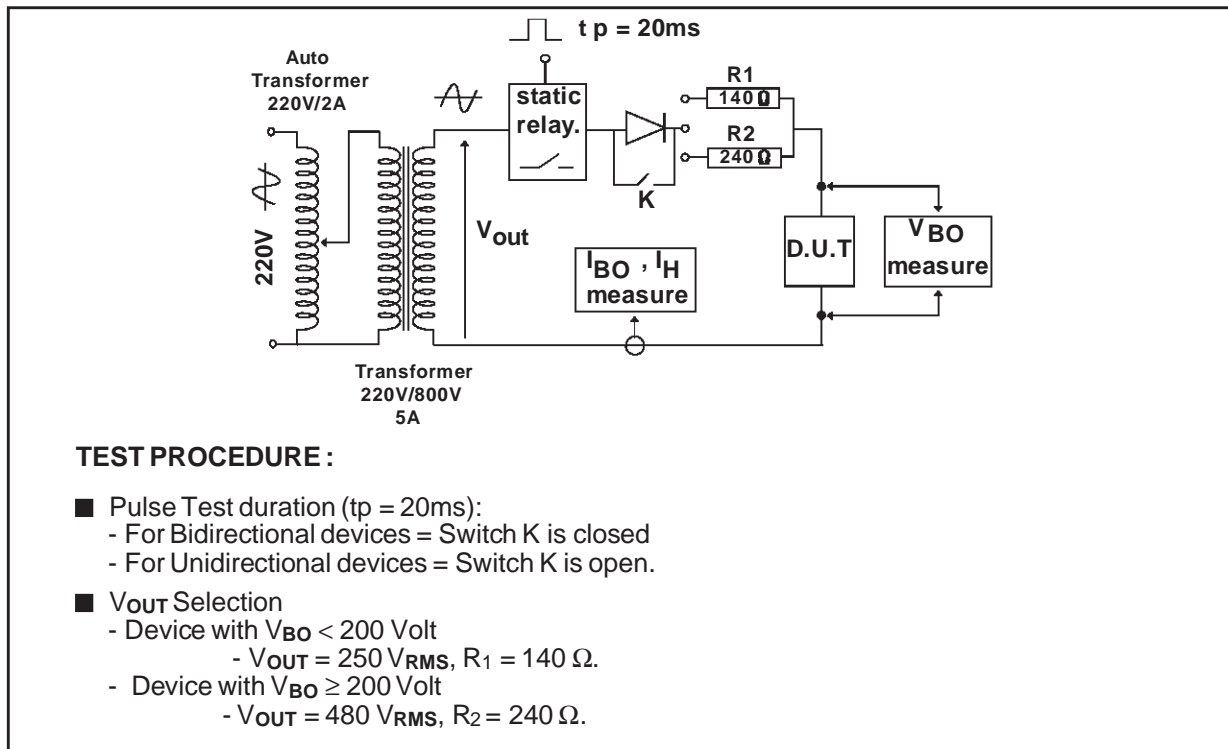
FUNCTIONAL HOLDING CURRENT (I$_H$) TEST CIRCUIT = GO - NOGO TEST.

R

D.U.T.

V$_{BAT}$ = - 48 V

- V$_P$

Surge generator

This is a GO-NOGO Test which allows to confirm the holding current (I$_H$) level in a functional test circuit.
This test can be performed if the reference test circuit can't be implemented.

TEST PROCEDURE :
1) Adjust the current level at the IH value by short circuiting the line and GND pins of the D.U.T.
2) Fire the D.U.T with a surge Current : Ipp = 10A , 10/1000 μs.
3) The D.U.T will come back to the OFF-State within a duration of 50 ms max.

Figure 1 : Surge peak current versus overload duration (typical values).

ITSM(A)
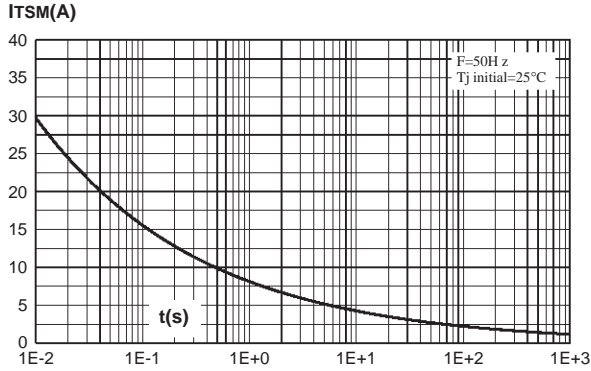
Figure 2 : Relative variation of holding current versus junction temperature.

$\dfrac{I_H \ [\ T_{amb}\ ]}{I_H\ [\ T_{amb}\ =25°C]}$

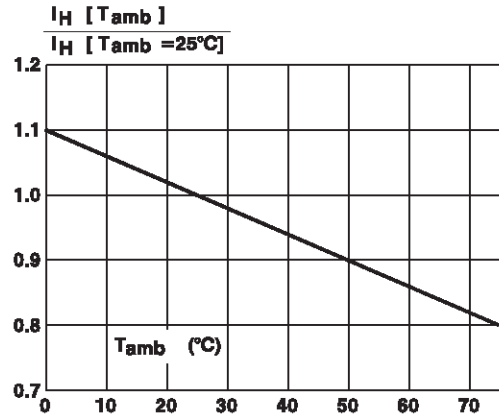**Figure 3** : Relative variation of breakdown voltage versus ambient temperature.
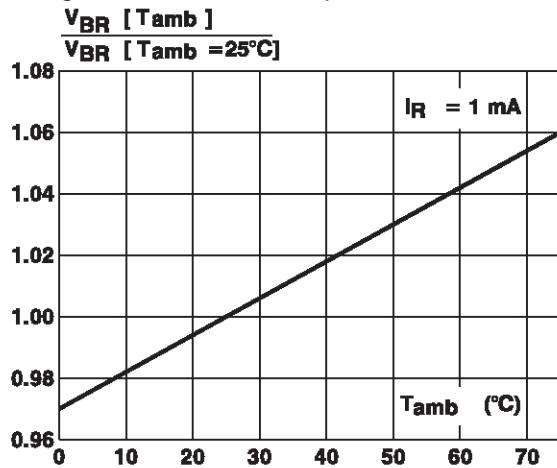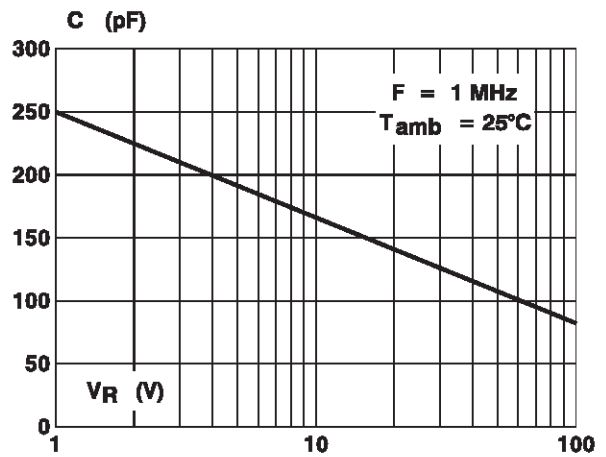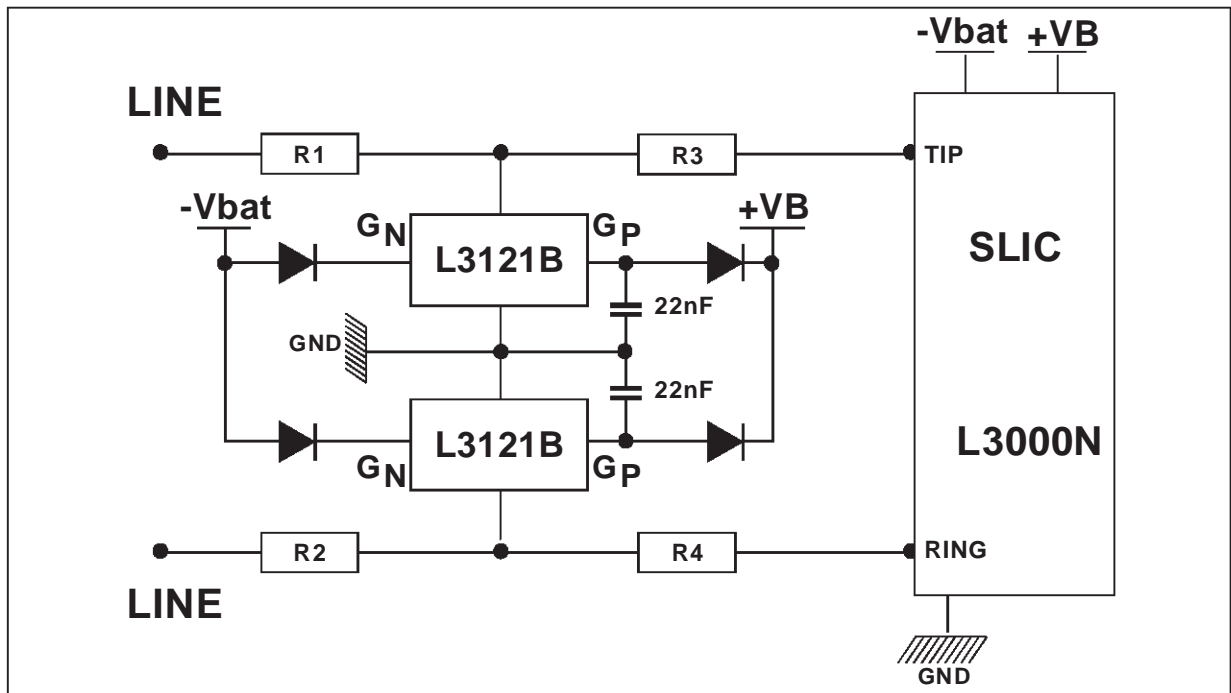
$\dfrac{V_{BR}\ [\ T_{amb}\ ]}{V_{BR}\ [\ T_{amb}\ =25°C]}$
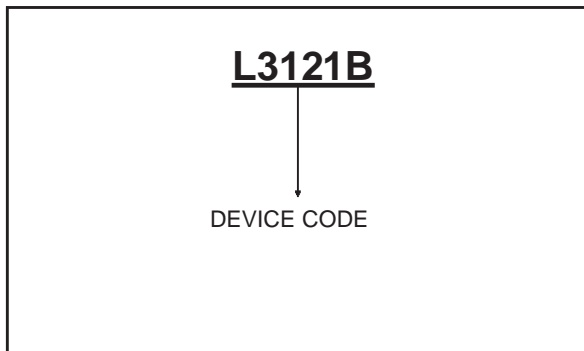

Figure 4 : Junction capacitance versus reverse applied voltage.

C (pF)

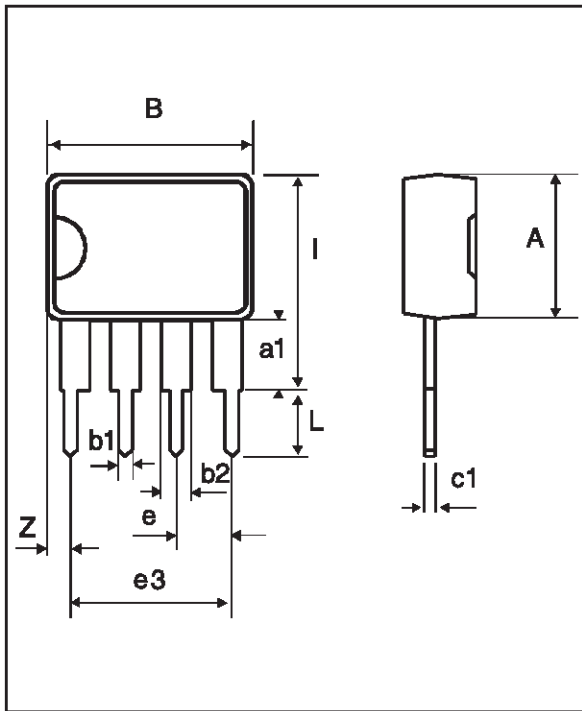![SGS-THOMSON MICROELECTRONICS]

Typical Slic Protection Concept.

ORDER CODE

L3121B

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DEVICE CODE

MARKING : Logo, Date Code, Part Number

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PACKAGE MECHANICAL DATA
SIP 4 (Plastic)

REF.	DIMENSIONS					
	Millimetres			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			7.10			0.280
a1	2.80			0.110		
B			10.15			0.400
b1		0.50			0.020	
b2	1.35		1.75	0.053		0.069
c1	0.38		0.50	0.015		0.020
e		2.54			0.100	
e3		7.62			0.200	
I			10.50			0.413
L		3.30			0.130	
Z			1.50			0.059

PACKAGING : Products supplied in antistatic tubes
WEIGHT : 0.55g

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